# imall

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Preferred Device

## **Silicon Controlled Rectifiers**

### **Reverse Blocking Thyristors**

Designed primarily for half-wave ac control applications, such as motor controls, heating controls and power supplies; or wherever half-wave silicon gate-controlled, solid-state devices are needed.

- Glass Passivated Junctions with Center Gate Geometry for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Blocking Voltage to 800 Volts
- Device Marking: Logo, Device Type, e.g., 2N6400, Date Code

*MAXIMUM RATINGS (T <sub>J</sub> = $25^{\circ}$ C ur	nless otherwise noted)
--	------------------------

Rating	Symbol	Value	Unit
$\begin{array}{l} \mbox{Peak Repetitive Off-State Voltage (Note 1.)} \\ (T_J = -40 \mbox{ to 125°C, Sine Wave} \\ 50 \mbox{ to 60 Hz; Gate Open)} \\ 2N6400 \\ 2N6401 \\ 2N6402 \\ 2N6403 \\ 2N6404 \\ 2N6405 \end{array}$	V <sub>DRM,</sub> V <sub>RRM</sub>	50 100 200 400 600 800	Volts
On-State RMS Current (180° Conduction Angles; T <sub>C</sub> = 100°C)	I <sub>T(RMS)</sub>	16	A
Average On-State Current (180° Conduction Angles; T <sub>C</sub> = 100°C)	I <sub>T(AV)</sub>	10	A
Peak Non-repetitive Surge Current (1/2 Cycle, Sine Wave 60 Hz, T <sub>J</sub> = 90°C)	I <sub>TSM</sub>	160	A
Circuit Fusing (t = 8.3 ms)	l <sup>2</sup> t	145	A <sup>2</sup> s
Forward Peak Gate Power (Pulse Width $\leq$ 1.0 $\mu$ s, T <sub>C</sub> = 100°C)	P <sub>GM</sub>	20	Watts
Forward Average Gate Power (t = 8.3 ms, $T_C = 100^{\circ}C$ )	P <sub>G(AV)</sub>	0.5	Watts
Forward Peak Gate Current (Pulse Width $\leq$ 1.0 $\mu$ s, T <sub>C</sub> = 100°C)	I <sub>GM</sub>	2.0	A
Operating Junction Temperature Range	ТJ	-40 to +125	°C
Storage Temperature Range	T <sub>stg</sub>	-40 to +150	°C

\*Indicates JEDEC Registered Data.

1. V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

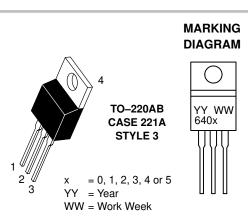


#### ON Semiconductor™

http://onsemi.com

#### SCRs 16 AMPERES RMS 50 thru 800 VOLTS





PIN ASSIGNMENT		
1	Cathode	
2	Anode	
3	Gate	
4	Anode	

#### ORDERING INFORMATION

Device	Package	Shipping
2N6400	TO220AB	500/Box
2N6401	TO220AB	500/Box
2N6402	TO220AB	500/Box
2N6403	TO220AB	500/Box
2N6404	TO220AB	500/Box
2N6405	TO220AB	500/Box

**Preferred** devices are recommended choices for future use and best overall value.

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#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Мах	Unit
Thermal Resistance, Junction to Case	$R_{ extsf{ heta}JC}$	1.5	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	TL	260	°C

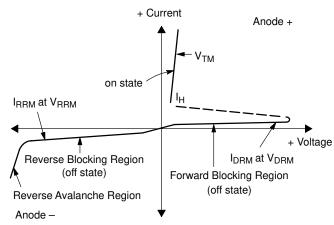
#### **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS			•		•	
*Peak Repetitive Forward or Reverse Blocking C (V <sub>AK</sub> = Rated V <sub>DRM</sub> or V <sub>RRM</sub> , Gate Open)	Current T <sub>J</sub> = 25°C T <sub>J</sub> = 125°C	I <sub>DRM</sub> , I <sub>RRM</sub>			10 2.0	μA mA
ON CHARACTERISTICS			•		•	
*Peak Forward On–State Voltage $(I_{TM} = 32 \text{ A Peak}, \text{Pulse Width} \leq 1 \text{ ms}, \text{Duty Cyl}$	ycle ≤ 2%)	V <sub>TM</sub>	-	-	1.7	Volts
*Gate Trigger Current (Continuous dc) $(V_D = 12 \text{ Vdc}, R_L = 100 \text{ Ohms})$	$T_{C} = 25^{\circ}C$ $T_{C} = -40^{\circ}C$	I <sub>GT</sub>		9.0 —	30 60	mA
*Gate Trigger Voltage (Continuous dc) (V <sub>D</sub> = 12 Vdc, R <sub>L</sub> = 100 Ohms)	$T_{C} = 25^{\circ}C$ $T_{C} = -40^{\circ}C$	V <sub>GT</sub>		0.7	1.5 2.5	Volts
Gate Non–Trigger Voltage $(V_D = 12 \text{ Vdc}, R_L = 100 \text{ Ohms})$	T <sub>C</sub> = +125°C	V <sub>GD</sub>	0.2	-	-	Volts
*Holding Current (V <sub>D</sub> = 12 Vdc, Initiating Current = 200 mA, Gate Open)	$T_{C} = 25^{\circ}C$ $T_{C} = -40^{\circ}C$	l <sub>Η</sub>		18 _	40 60	mA
Turn-On Time $(I_{TM} = 16 \text{ A}, I_{GT} = 40 \text{ mAdc}, V_D = \text{Rated } V_{DRM}$	)	t <sub>gt</sub>	-	1.0	-	μs
Turn-Off Time ( $I_{TM}$ = 16 A, $I_{R}$ = 16 A, $V_{D}$ = Rated $V_{DRM}$ )	T <sub>C</sub> = 25°C T <sub>J</sub> = +125°C	tq	-	15 35	-	μs
DYNAMIC CHARACTERISTICS						
Critical Rate-of-Rise of Off-State Voltage $(V_D = Rated V_{DRM}, Exponential Waveform)$	T <sub>J</sub> = +125°C	dv/dt	-	50	-	V/µs

\*Indicates JEDEC Registered Data.

#### Voltage Current Characteristic of SCR

Symbol	Parameter
V <sub>DRM</sub>	Peak Repetitive Off State Forward Voltage
I <sub>DRM</sub>	Peak Forward Blocking Current
V <sub>RRM</sub>	Peak Repetitive Off State Reverse Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
V <sub>TM</sub>	Peak On State Voltage
Ι <sub>Η</sub>	Holding Current



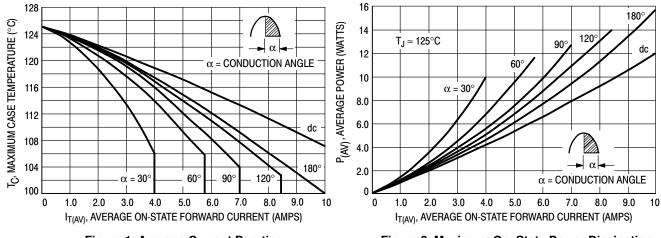
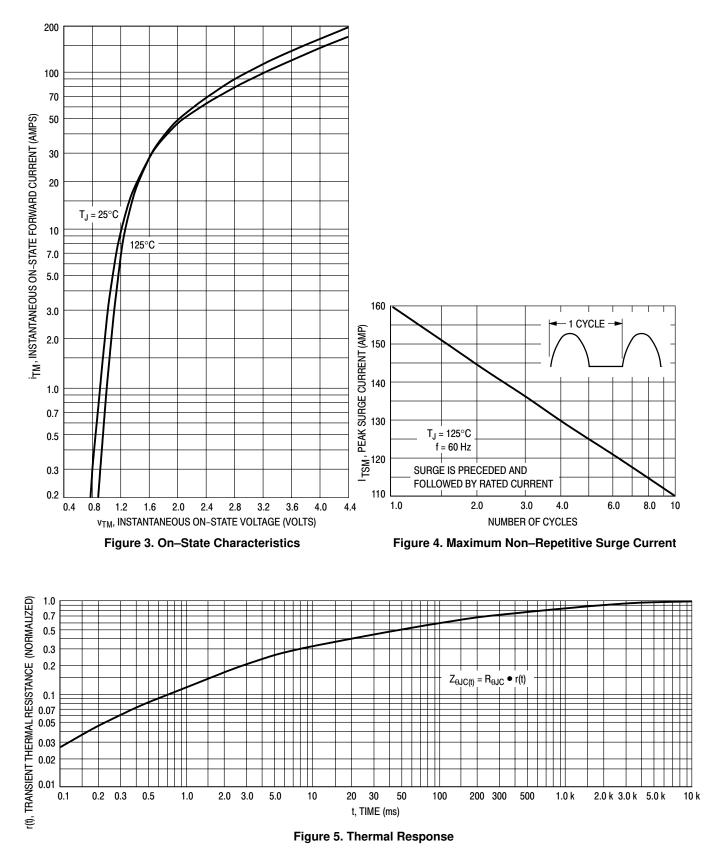
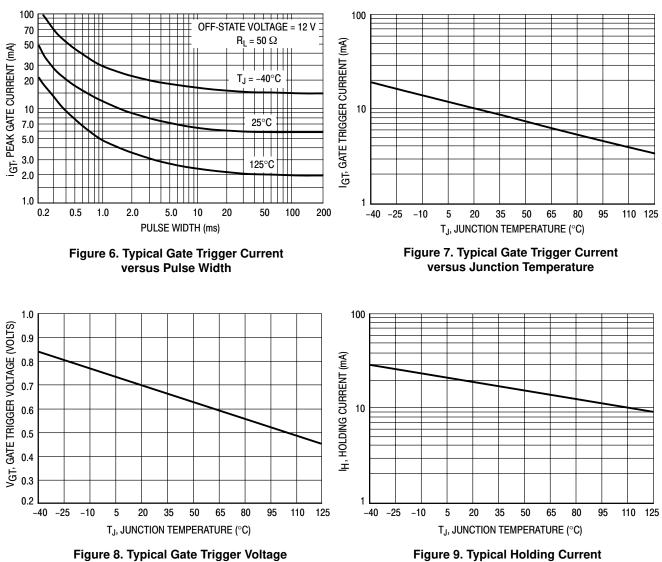


Figure 1. Average Current Derating

Figure 2. Maximum On–State Power Dissipation



#### **TYPICAL CHARACTERISTICS**

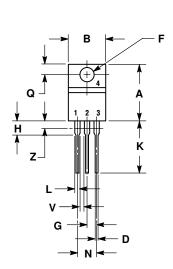


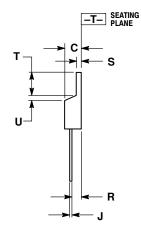
versus Junction Temperature

Figure 9. Typical Holding Current versus Junction Temperature

#### PACKAGE DIMENSIONS

TO-220AB CASE 221A-07 **ISSUE AA** 





NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIN	IMETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.570	0.620	14.48	15.75	
В	0.380	0.405	9.66	10.28	
С	0.160	0.190	4.07	4.82	
D	0.025	0.035	0.64	0.88	
F	0.142	0.147	3.61	3.73	
G	0.095	0.105	2.42	2.66	
н	0.110	0.155	2.80	3.93	
J	0.014	0.022	0.36	0.55	
Κ	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
Ν	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.39	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
V	0.045		1.15		
Z		0.080		2.04	

### <u>Notes</u>

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